

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions and listings of claims in the application:

1. (Withdrawn) A circuit comprising:
a MOS transistor having a cap layer comprised of a high dielectric constant material.
2. (Withdrawn) The circuit of Claim 1 wherein said high dielectric constant material is hafnium silicon oxynitride.
3. (Currently Amended) A circuit comprising:
a PMOS transistor, said PMOS transistor having a gate oxide, a lightly doped drain coupled to said gate oxide, and a cap layer coupled to a majority of a top surface of said lightly doped drain but separated from said gate oxide, said cap layer comprised of a high dielectric constant material ~~The circuit of Claim 1 wherein said MOS transistor is a PMOS transistor.~~
4. (Withdrawn) The circuit of Claim 1 wherein said MOS transistor is a NMOS transistor.

5. (Withdrawn) A MOS transistor comprising:

a cap layer comprised of a high dielectric constant material.

6. (Withdrawn) The MOS transistor of Claim 5 wherein said high dielectric constant material is hafnium silicon oxynitride.

7. (Withdrawn) The MOS transistor of Claim 5 wherein said MOS transistor is a NMOS transistor.

8. (Canceled)

9. (Currently Amended) A PMOS transistor comprising:

a gate oxide;

a lightly doped drain coupled to said gate oxide; and

a cap layer coupled to a majority of a top surface of said lightly doped drain but separated from said gate oxide, said cap layer comprised of a high dielectric constant material.

10. (Original) The PMOS transistor of Claim 9 wherein said high dielectric constant material is hafnium silicon oxynitride.

11. (Withdrawn) A PMOS transistor comprising:

a gate oxide;

a lightly doped drain coupled to said gate oxide; and

a cap layer comprised of hafnium silicon oxynitride coupled to a majority of a top surface of said lightly doped drain but separated from said gate oxide.